

General Description

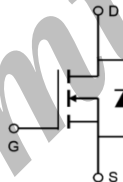
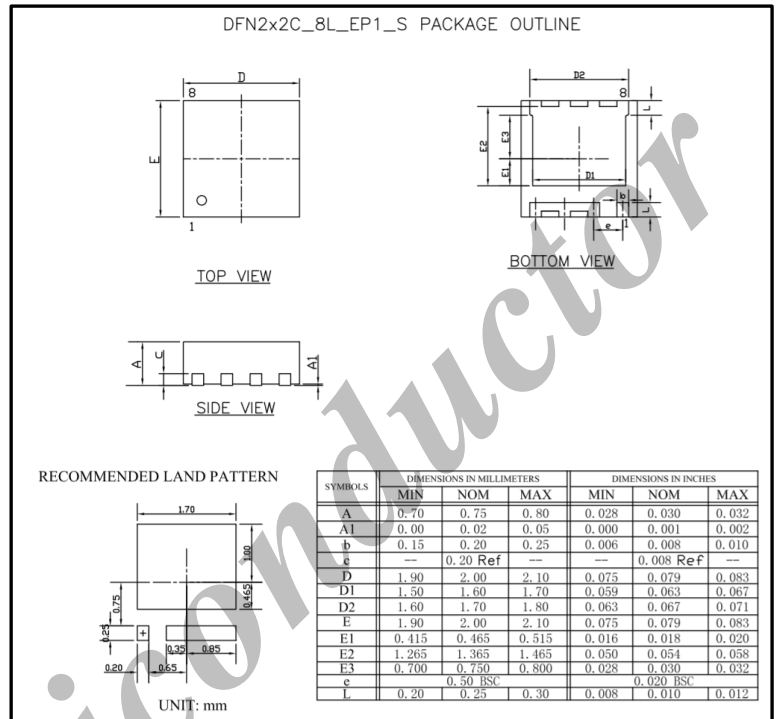
APN2392 combines advanced MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is most suitable to load-switch or PWM applications.

Applications

- DC/DC converter for portable devices
- Load switch

Product Summary

V_{DS}	100V
I_D (at $V_{GS} = 10V$)	8A
$R_{DS(ON)}$ (at $V_{GS} = 10V$)	< 32m Ω
$R_{DS(ON)}$ (at $V_{GS} = 4.5V$)	< 39m Ω



Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current $T_A = 25^\circ\text{C}$ $T_A = 70^\circ\text{C}$	I_D	8	A
		6	
Pulsed Drain Current *	I_{DM}	32	
Power Dissipation $T_A = 25^\circ\text{C}$ $T_A = 70^\circ\text{C}$	P_D	4.1	W
		2.6	
Thermal Resistance. Junction- to-Ambient ($t \leq 10s$) (Steady-State)	$R_{\theta JA}$	30	$^\circ\text{C/W}$
		55	
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 to 150	

* Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)} = 150^\circ\text{C}$. Ratings are based on low frequency and duty cycles to keep initial $T_J = 25^\circ\text{C}$.

Electrical Characteristics $T_j = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DS}	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	100			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=100\text{V}$, $V_{GS}=0\text{V}$			1	μA
		$V_{DS}=100\text{V}$, $V_{GS}=0\text{V}$, $T_j=55^\circ\text{C}$			5	
Gate-Body leakage current	I_{GSS}	$V_{DS}=0\text{V}$, $V_{GS}=\pm 20\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	1.4		2.4	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10\text{V}$, $I_D=8\text{A}$			32	m Ω
		$V_{GS}=10\text{V}$, $I_D=8\text{A}$, $T_j=125^\circ\text{C}$			57	
		$V_{GS}=4.5\text{V}$, $I_D=6\text{A}$			39	
Forward Transconductance	g_{FS}	$V_{DS}=5\text{V}$, $I_D=8\text{A}$		25		S
Input Capacitance	C_{iss}	$V_{GS}=0\text{V}$, $V_{DS}=50\text{V}$, $f=1\text{MHz}$		840		pF
Output Capacitance	C_{oss}			64		
Reverse Transfer Capacitance	C_{rss}			4		
Gate Resistance	R_g	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$		1.4		Ω
Total Gate Charge	$Q_g(10\text{V})$	$V_{GS}=10\text{V}$, $V_{DS}=50\text{V}$, $I_D=8\text{A}$		12.8	25	nC
Total Gate Charge	$Q_g(4.5\text{V})$			6.1	12	
Gate Source Charge	Q_{gs}			2.1		
Gate Drain Charge	Q_{gd}			1.8		
Output Charge	Q_{oss}	$V_{GS}=0\text{V}$, $V_{DS}=50\text{V}$		11		ns
Turn-On Delay Time	$t_{D(on)}$	$V_{GS}=10\text{V}$, $V_{DS}=50\text{V}$, $R_L=5.85\Omega$, $R_{GEN}=3\Omega$		7		
Turn-On Rise Time	t_r			8		
Turn-Off Delay Time	$t_{D(off)}$			24		
Turn-Off Fall Time	t_f			3		
Body Diode Reverse Recovery Time	t_{rr}	$I_F=8\text{A}$, $dI/dt=500\text{A}/\mu\text{s}$		20		ns
Body Diode Reverse Recovery Charge	Q_{rr}			70		nC
Maximum Body-Diode Continuous Current	I_S				5	A
Diode Forward Voltage	V_{SD}	$I_S=1\text{A}$, $V_{GS}=0\text{V}$			1	V

Ordering Information

Ordering Part Number	Package	MOQ
APN2392	DFN 2x2C	3,000 pcs / reel

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- Typical Characteristics

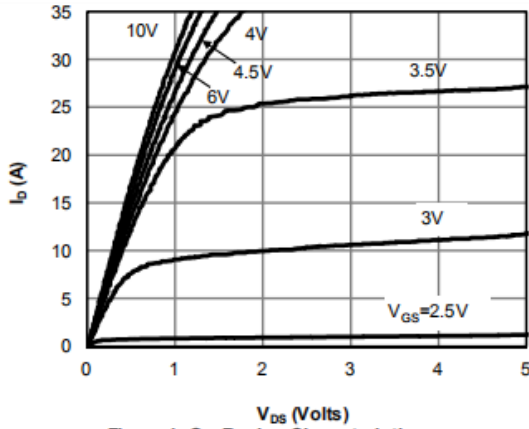


Figure 1: On-Region Characteristics

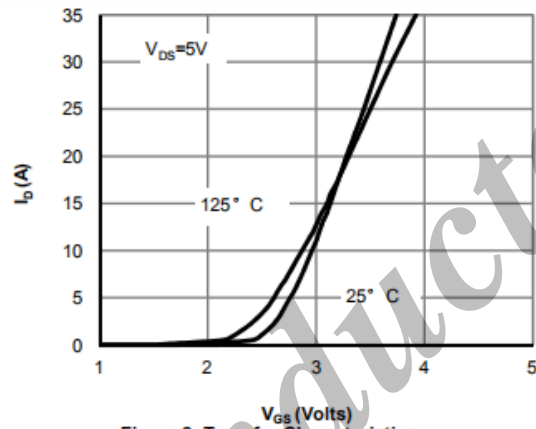


Figure 2: Transfer Characteristics

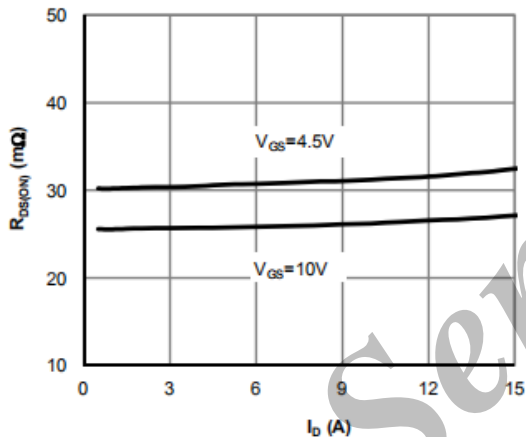


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

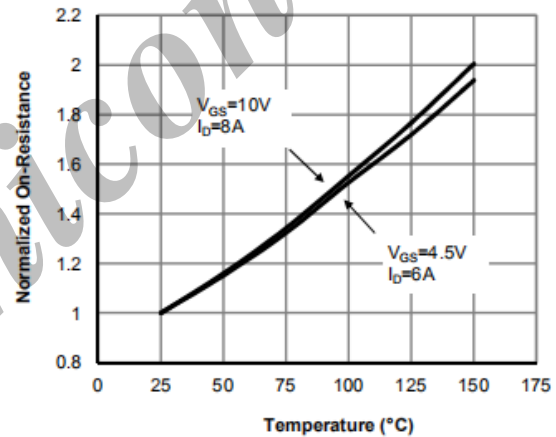


Figure 4: On-Resistance vs. Junction Temperature

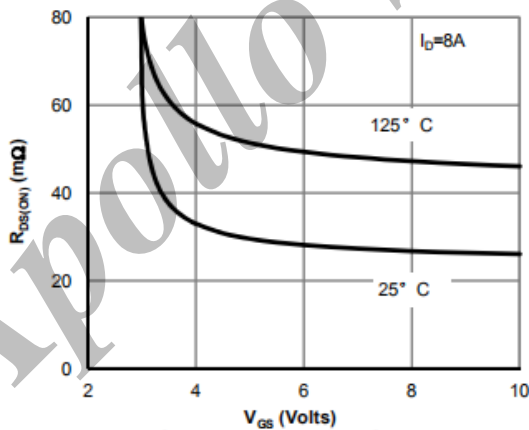


Figure 5: On-Resistance vs. Gate-Source Voltage

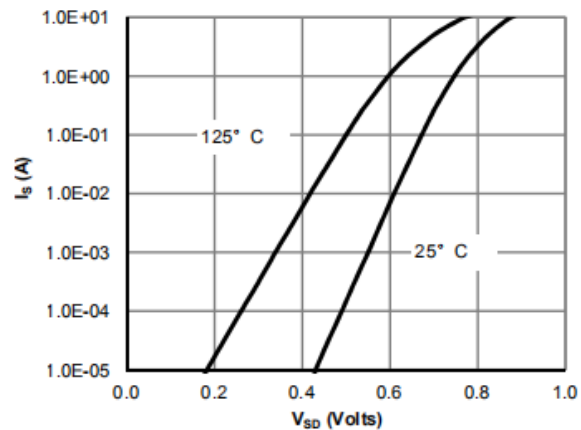


Figure 6: Body-Diode Characteristics

The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

• **Typical Characteristics**

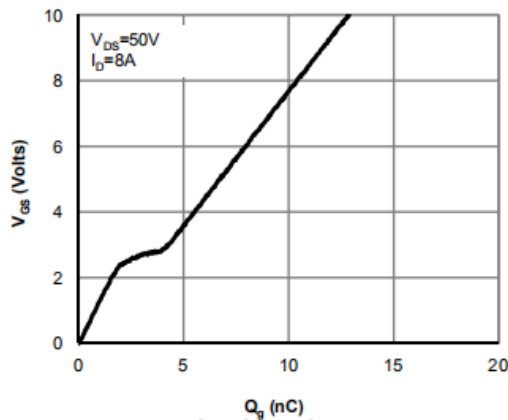


Figure 7: Gate-Charge Characteristics

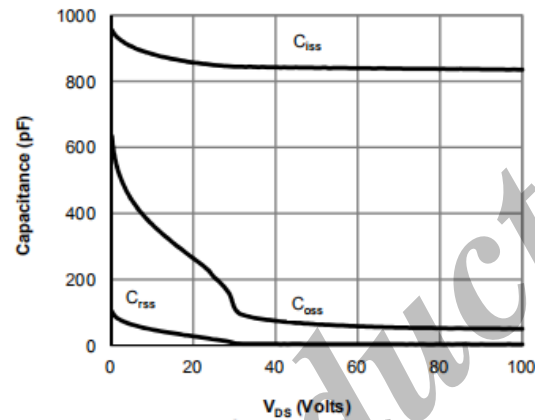


Figure 8: Capacitance Characteristics

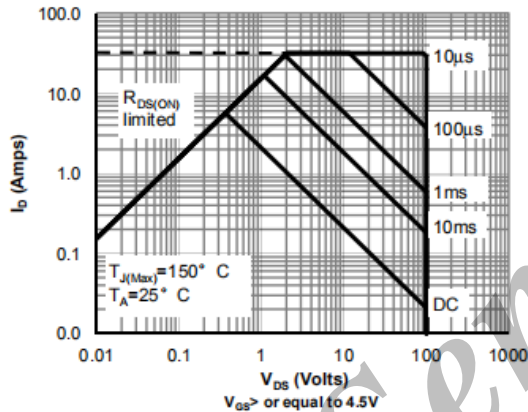


Figure 9: Maximum Forward Biased Safe Operating Area

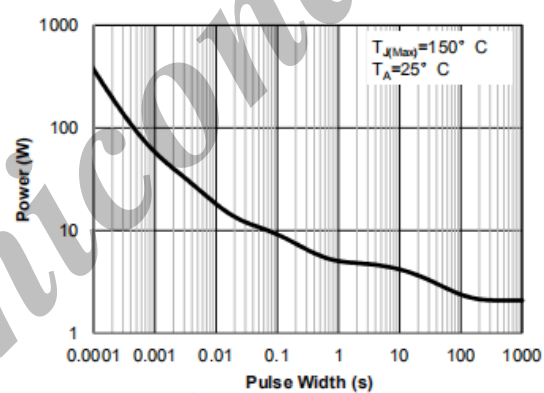


Figure 10: Single Pulse Power Rating Junction-to-Ambient

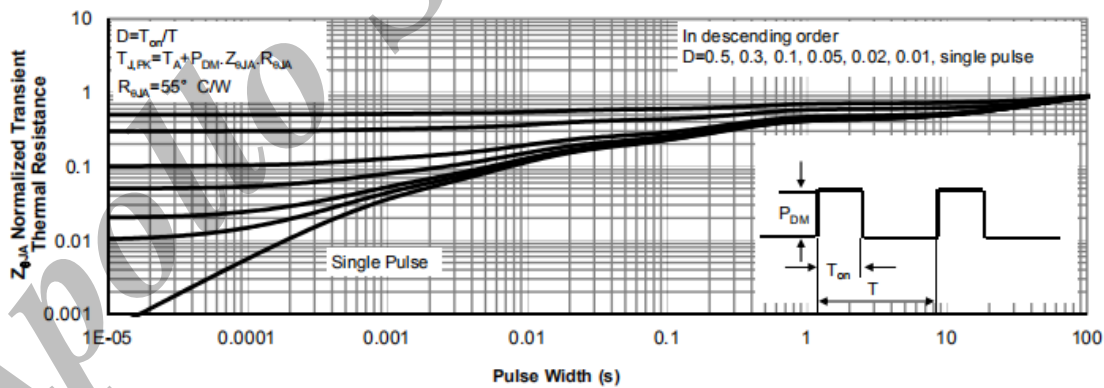


Figure 11: Normalized Maximum Transient Thermal Impedance

The curves in Figures 9 to 11 are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, assuming a maximum junction temperature of $T_{j(MAX)}=150^{\circ}\text{C}$. The SOA curve provides a single pulse rating.

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